23. (New) A method of inhibiting delamination of a cavitation layer in a multi-layered integrated circuit comprising the steps of:

forming a conductive layer;

electrically isolating a first portion of the conductive layer from a second portion thereof with a shielding element; and

depositing the cavitation layer over portions of the first portion and the second portion, and over the shielding element.

24. (New) The method of claim 23, wherein the step of electrically isolating comprises the step of growing a field oxide layer within a portion of the conductive layer.

25. (New) The method of claim 24, further comprising the step of depositing a polycrystalline silicon layer over the field oxide layer.

26. (New) The method of claim 23, wherein the cavitation layer comprises Tantalum.

27. (New) The method of claim 23, wherein the conductive layer comprises a doped region in a substrate.